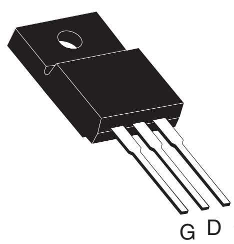
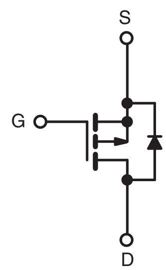
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	V_{GS} = - 10 V	1.5
Q_g (Max.) (nC)	15	
Q_{gs} (nC)	3.2	
Q_{gd} (nC)	8.4	
Configuration	Single	

TO-220 FULLPAK





P-Channel MOSFET

FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV_{RMS} (t = 60 s; f = 60 Hz)
- Sink to Lead Creepage Dist. = 4.8 mm
- P-Channel
- Dynamic dV/dt
- Low Thermal Resistance
- Lead (Pb)-free Available

Pb Available
RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI9620GPbF
	SiHFI9620G-E3
SnPb	IRFI9620G
	SiHFI9620G

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

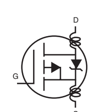
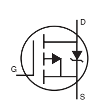
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	- 200	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	T_C = 25 °C	I_D	- 3.0	A
		T_C = 100 °C		- 1.9	
Pulsed Drain Current[a]			I_{DM}	- 12	
Linear Derating Factor				0.24	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	80	mJ
Repetitive Avalanche Current[a]			I_{AR}	- 3.0	A
Repetitive Avalanche Energy[a]			E_{AR}	3.0	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	30	W
Peak Diode Recovery dV/dt[c]			dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[d]	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. V_{DD} = - 50 V, starting T_J = 25 °C, L = 13 mH, R_G = 25 Ω, I_{AS} = - 3.0 A (see fig. 12).
c. $I_{SD} \le$ - 3.9 A, dI/dt ≤ 95 A/µs, $V_{DD} \le V_{DS}$, $T_J \le$ 150 °C.
d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	4.1	

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = - 1 mA	-	- 0.22	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 200 V, V_{GS} = 0 V	-	-	- 100	µA
		V_{DS} = - 160 V, V_{GS} = 0 V, T_J = 125 °C	-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = - 10 V; I_D = - 1.8 A[b]	-	-	1.5	Ω
Forward Transconductance	g_{fs}	V_{DS} = - 50 V, I_D = - 1.8 A[b]	1.3	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 15 V, f = 1.0 MHz, see fig. 5	-	340	-	pF
Output Capacitance	C_{oss}		-	110	-	
Reverse Transfer Capacitance	C_{rss}		-	33	-	
Drain to Sink Capacitance	C	f = 1 MHz	-	12	-	
Total Gate Charge	Q_g	V_{GS} = - 10 V; I_D = - 2.1 A, V_{DS} = - 160 V, see fig. 6 and 13[b]	-	-	15	nC
Gate-Source Charge	Q_{gs}		-	-	3.2	
Gate-Drain Charge	Q_{gd}		-	-	8.4	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 100 V, I_D = - 3.9 A, R_G = 18 Ω, R_D= 24 Ω, see fig. 10[b]	-	8.8	-	ns
Rise Time	t_r		-	27	-	
Turn-Off Delay Time	$t_{d(off)}$		-	7.3	-	
Fall Time	t_f		-	19	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	- 3.0	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	- 12	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = - 3.0 A, V_{GS} = 0 V[b]	-	-	- 6.3	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = - 3.9 A, dI/dt = 100 A/µs[b]	-	150	300	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.97	2.0	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

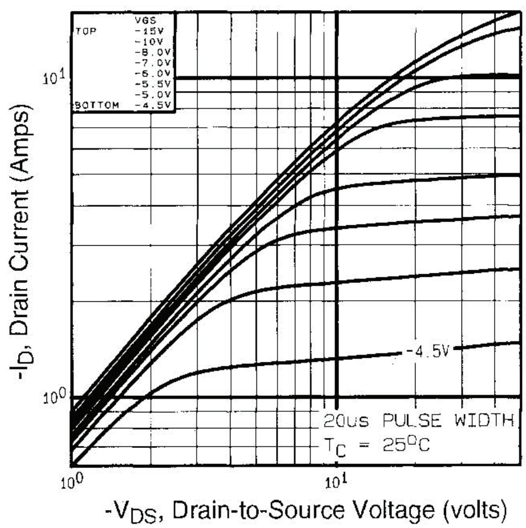


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

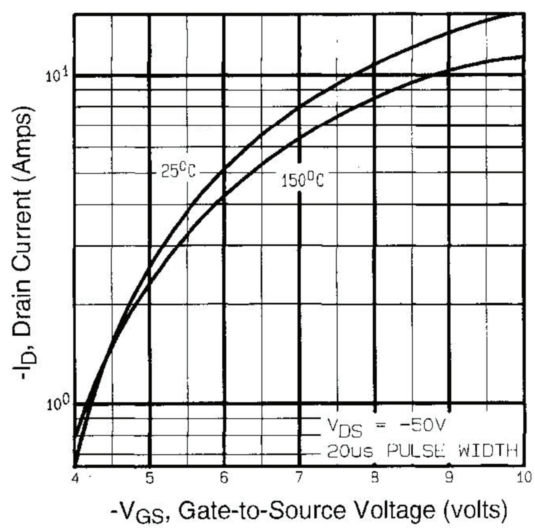


Fig. 3 - Typical Transfer Characteristics

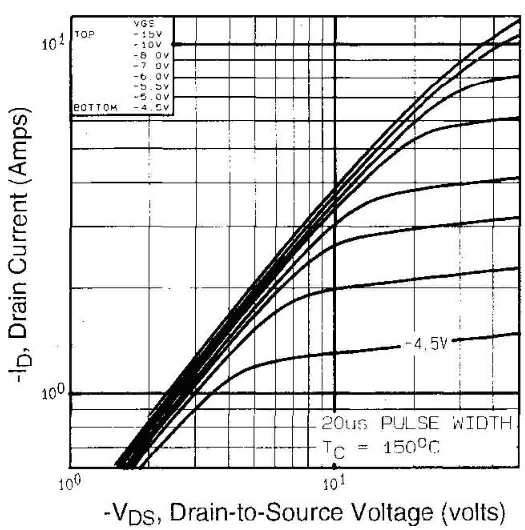


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

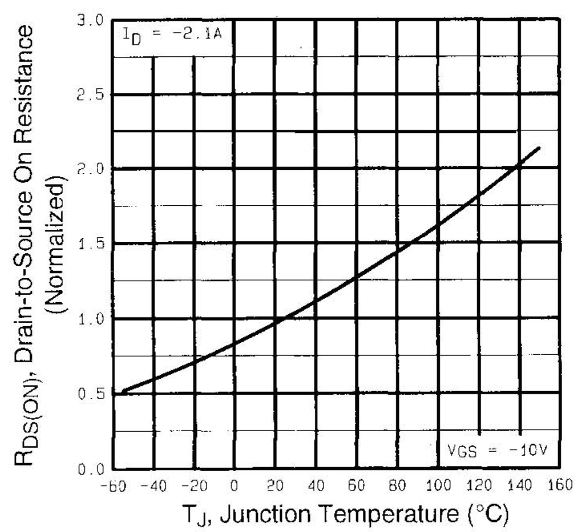


Fig. 4 - Normalized On-Resistance vs. Temperature

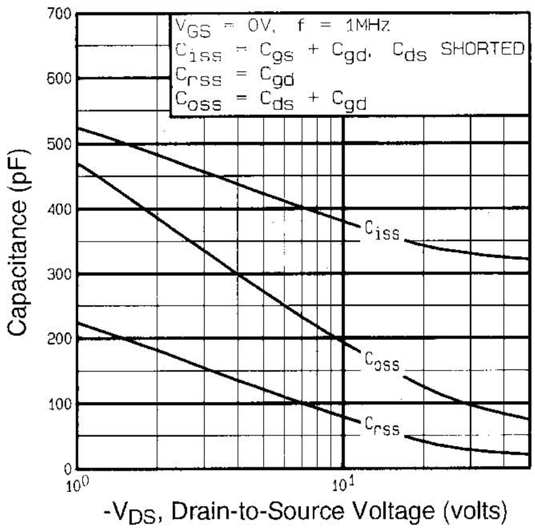


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

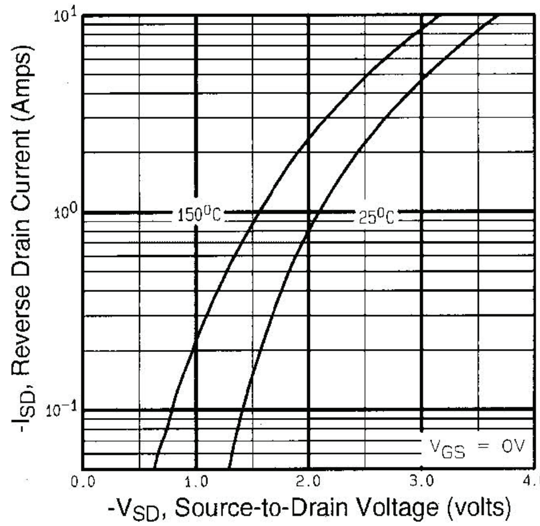


Fig. 7 - Typical Source-Drain Diode Forward Voltage

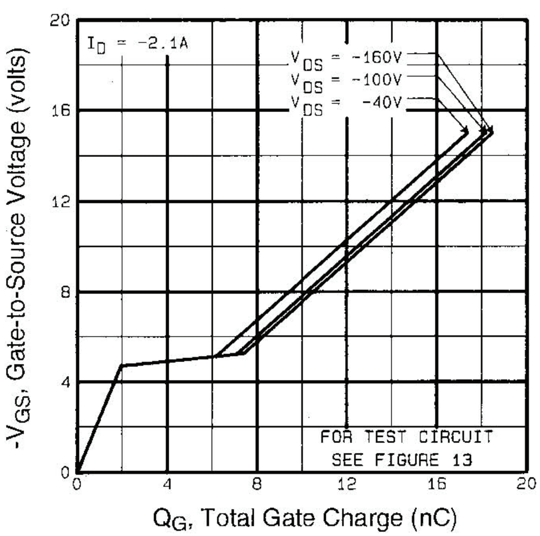


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

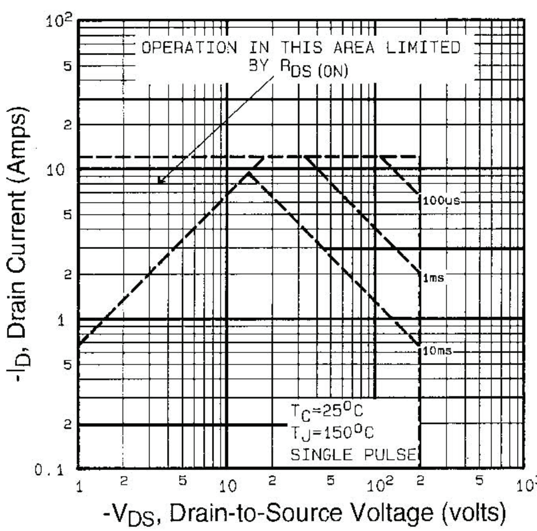


Fig. 8 - Maximum Safe Operating Area

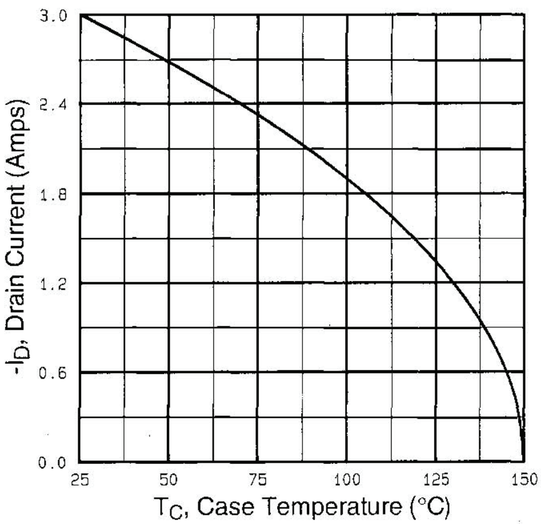


Fig. 9 - Maximum Drain Current vs. Case Temperature

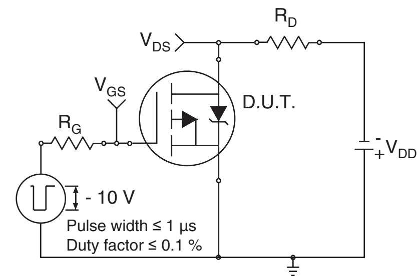


Fig. 10a - Switching Time Test Circuit

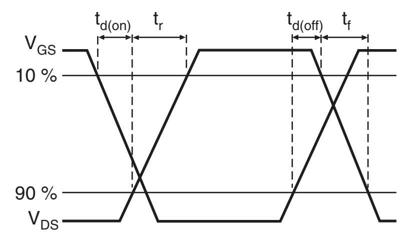


Fig. 10b - Switching Time Waveforms

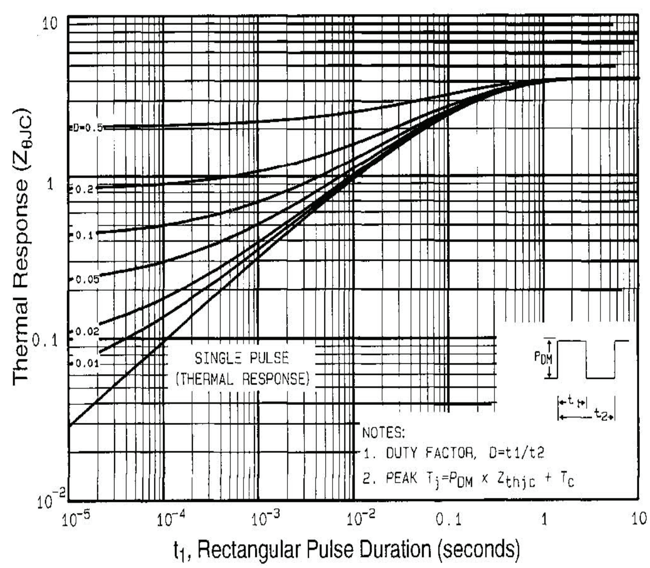


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

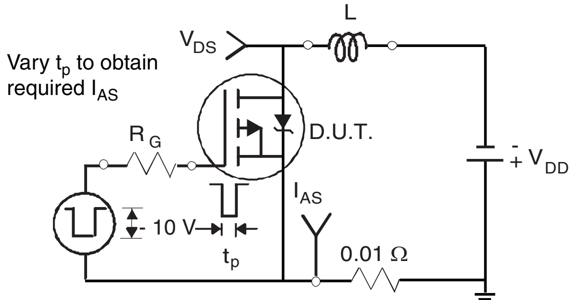


Fig. 12a - Unclamped Inductive Test Circuit

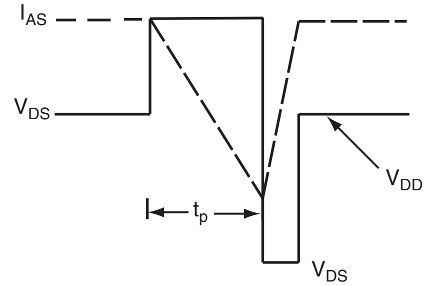


Fig. 12b - Unclamped Inductive Waveforms

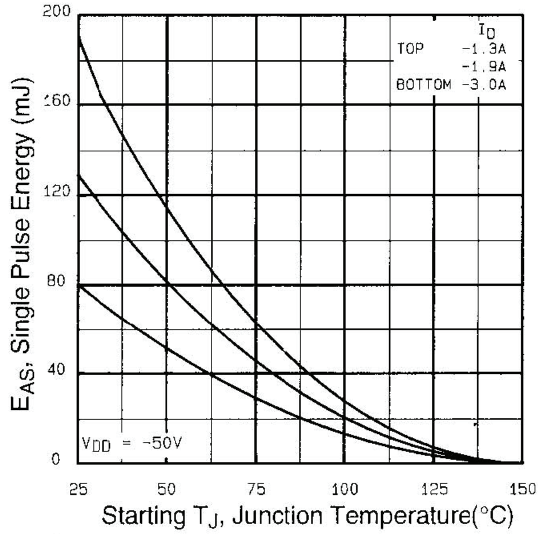


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

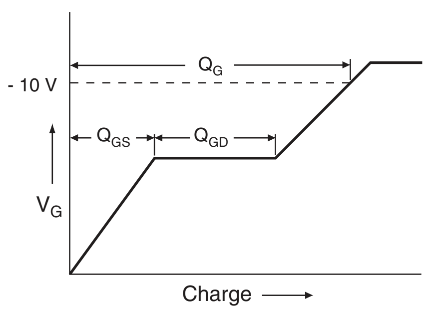


Fig. 13a - Basic Gate Charge Waveform

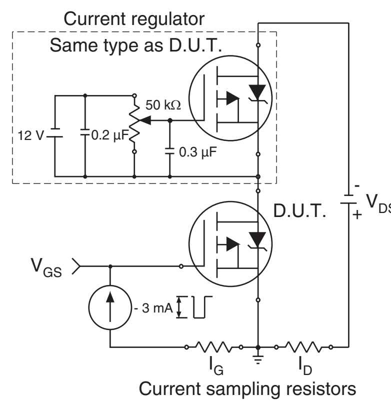
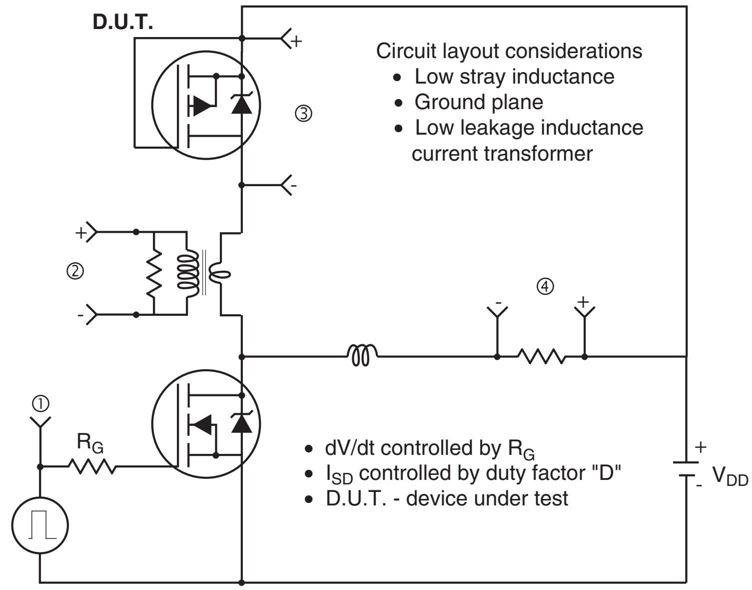
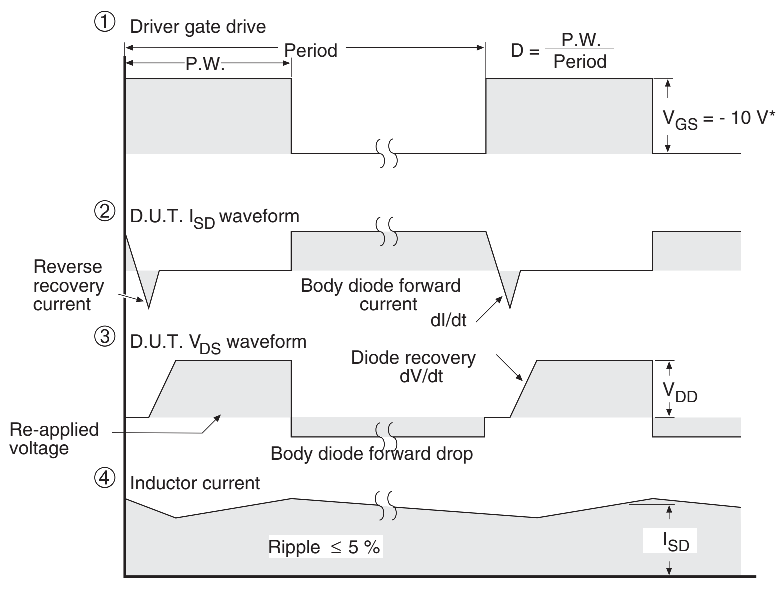


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



• Compliment N-Channel of D.U.T. for driver



* V_{GS} = - 5 V for logic level and - 3 V drive devices

Fig. 14 - For P-Channel

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